



# 2SC6082

## Bipolar Transistor 50V, 15A, Low VCE (sat) NPN TO-220F-3SG

ON Semiconductor®

<http://onsemi.com>

### Applications

- High-speed switching applications (switching regulator, driver circuit)

### Features

- Adoption of MBIT process
- Low collector-to-emitter saturation voltage
- Large current capacitance
- High-speed switching

### Specifications

Absolute Maximum Ratings at Ta=25°C

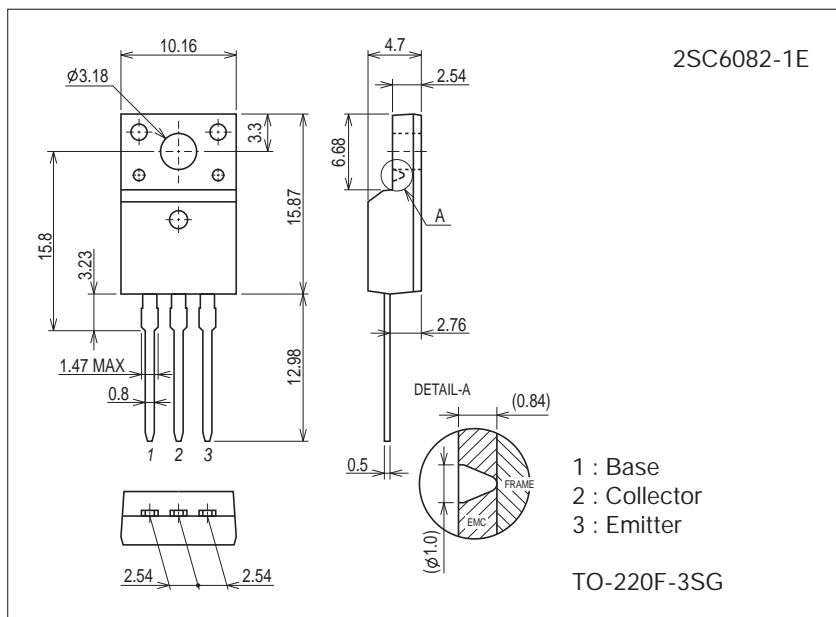
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		60	V
Collector-to-Emitter Voltage	VCES		60	V
	VCEO		50	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		15	A
Collector Current (Pulse)	ICP	PW≤10μs, duty cycle≤1%	20	A
Base Current	IB		3	A
Collector Dissipation	PC		2	W
		Tc=25°C	23	W
Junction Temperature	TJ		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### Package Dimensions

unit : mm (typ)

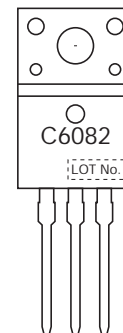
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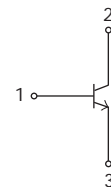
### Product & Package Information

- Package : TO-220F-3SG
- JEITA, JEDEC : SC-67
- Minimum Packing Quantity : 50 pcs./magazine

### Marking



### Electrical Connection

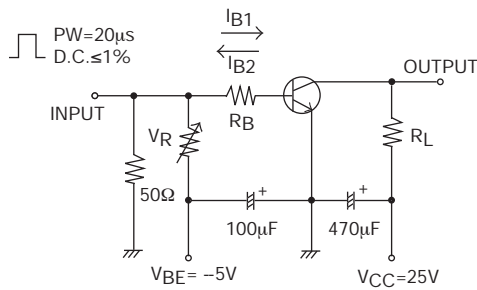


## 2SC6082

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=40V, I_E=0A$			10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4V, I_C=0A$			10	$\mu A$
DC Current Gain	$h_{FE1}$	$V_{CE}=2V, I_C=330mA$	200		560	
	$h_{FE2}$	$V_{CE}=2V, I_C=10A$	50			
Gain-Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=2A$		195		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1MHz$		85		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=7.5A, I_B=375mA$		200	400	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=7.5A, I_B=375mA$			1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0A$	60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100\mu A, R_{BE}=0\Omega$	60			V
	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0A$	6			V
Turn-On Time	$t_{on}$	See specified Test Circuit		52		ns
Storage Time	$t_{stg}$			560		ns
Fall Time	$t_f$			37		ns

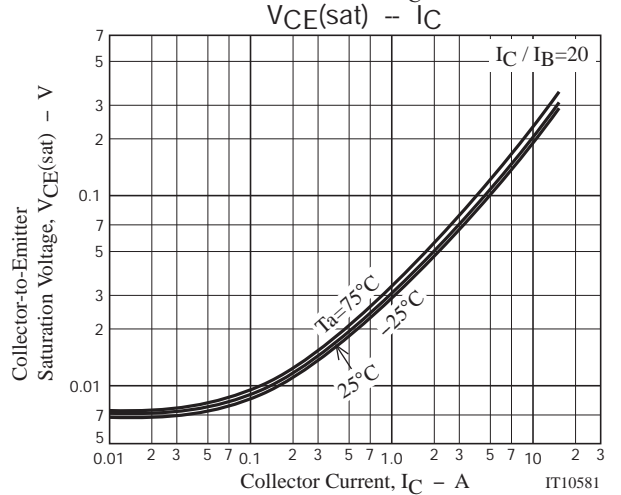
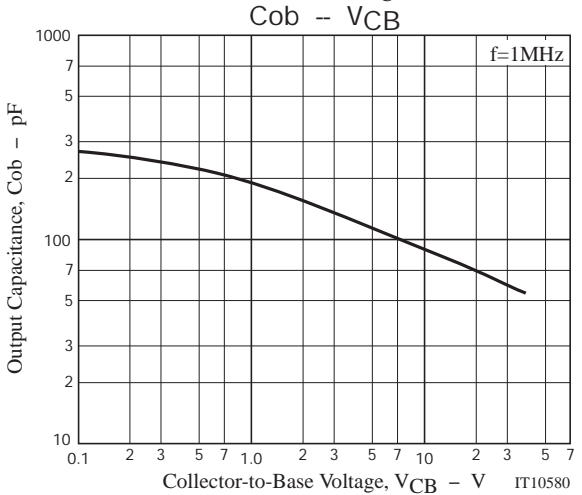
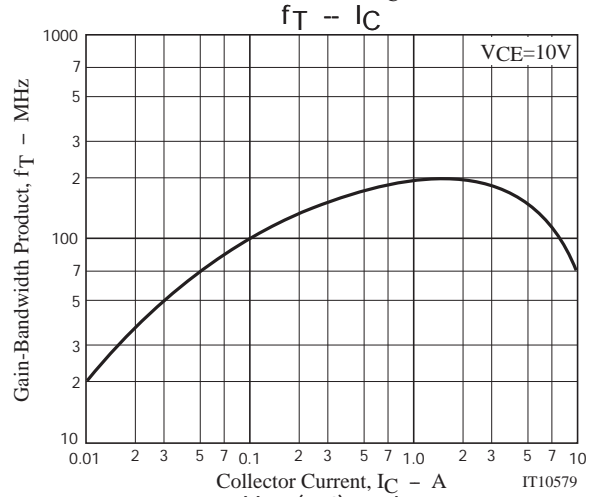
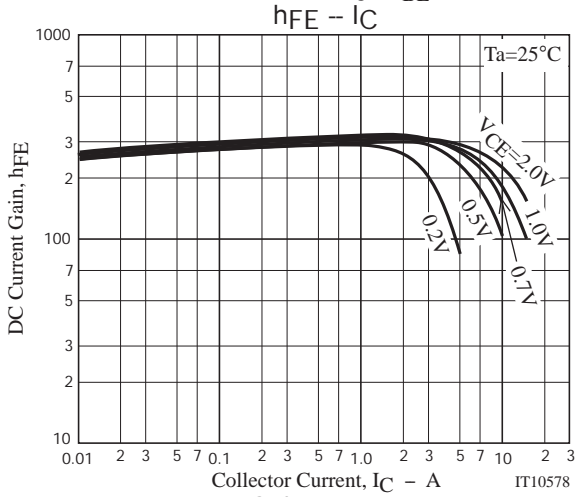
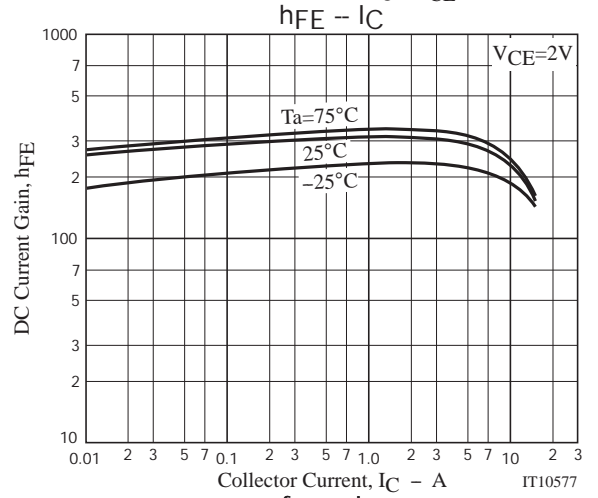
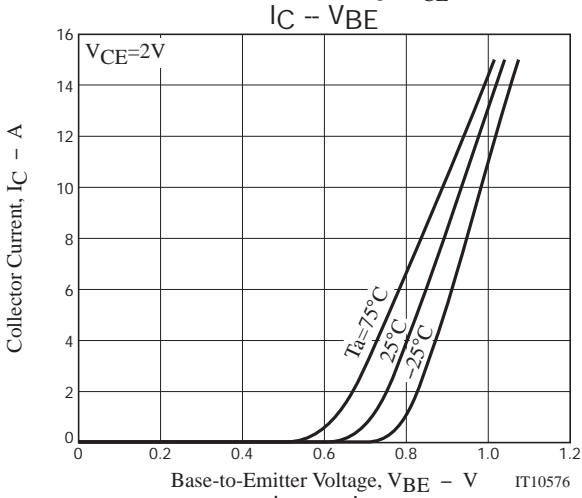
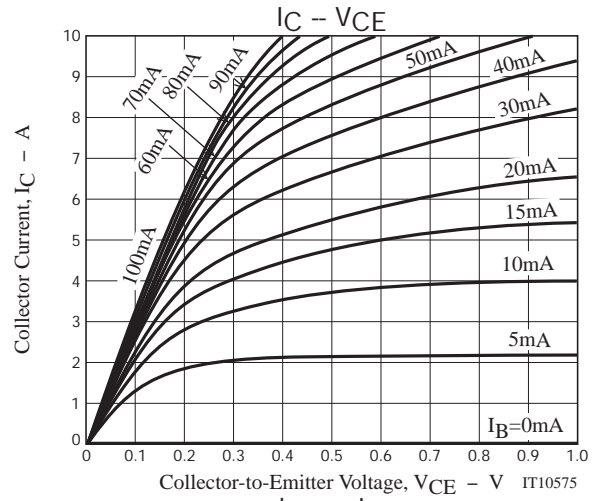
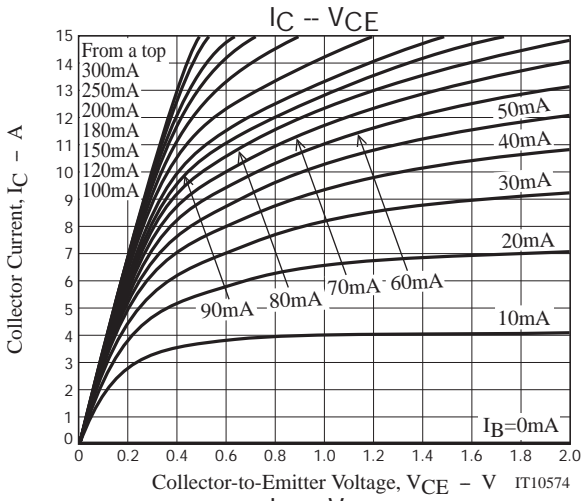
### Switching Time Test Circuit

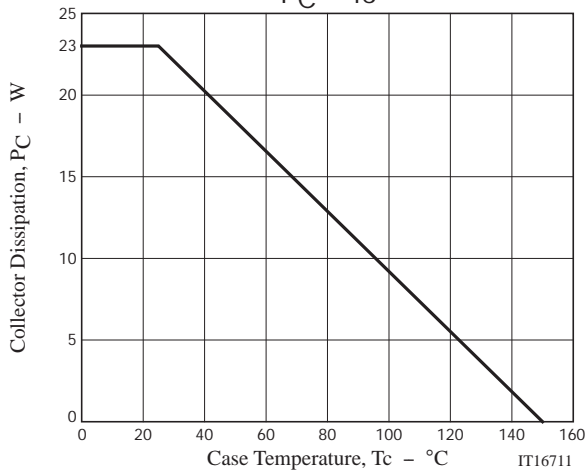
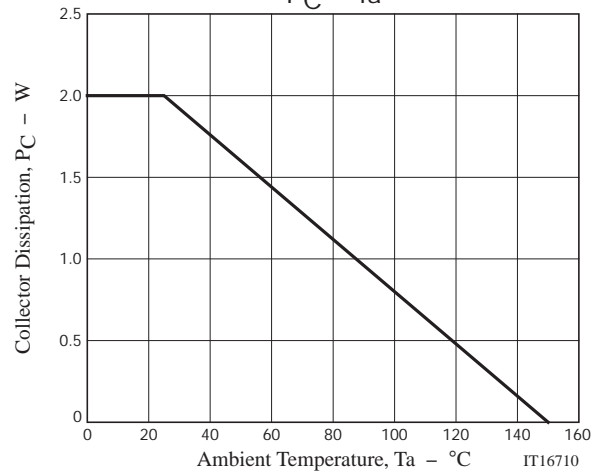
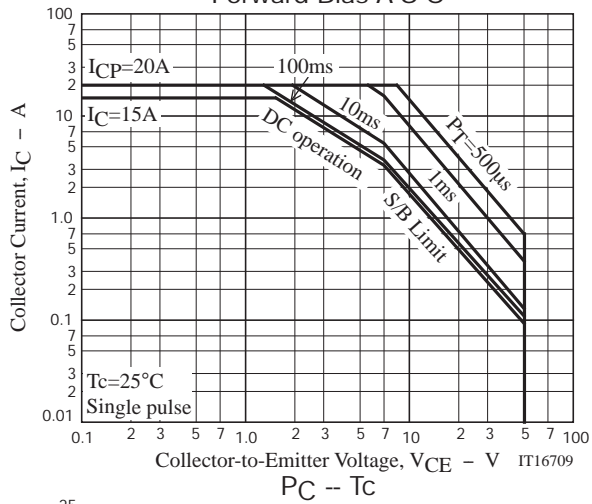
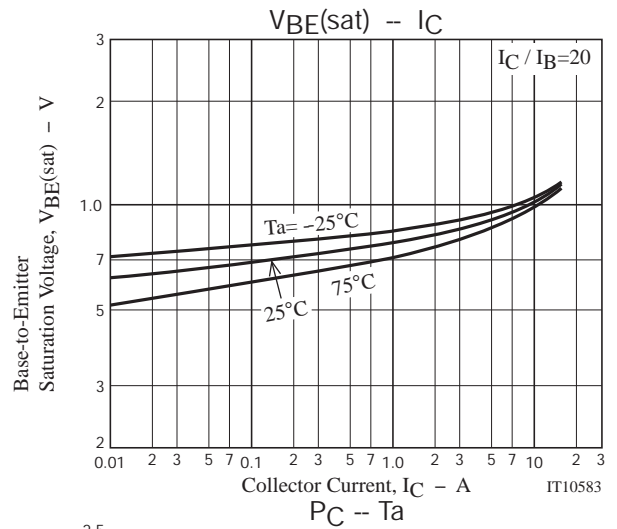
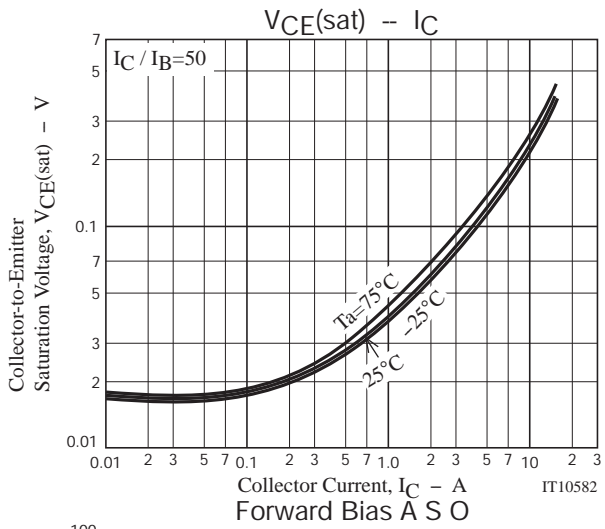


$$I_C = 20I_{B1} = -20I_{B2} = 5A$$

### Ordering Information

Device	Package	Shipping	memo
2SC6082-1E	TO-220F-3SG	50pcs./magazine	Pb Free





Magazine Specification

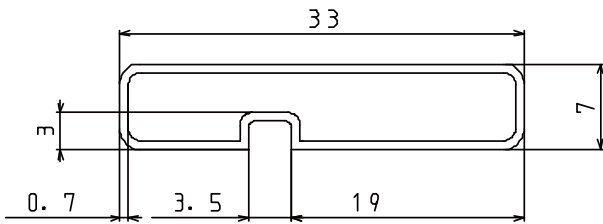
2SC6082-1E

1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (pcs)			Packing format	
		Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3SG	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

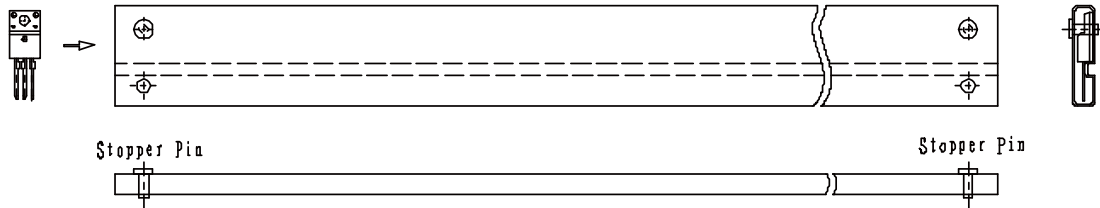
2. Magazine dimensions

(unit:mm)

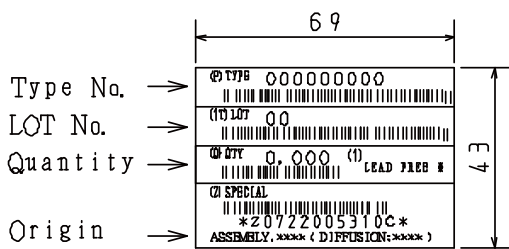


Tolerance=±0.3mm  
 Thickness=0.7±0.2mm  
 Length =532.5±2mm  
 Material =PVC (Antistatic treatment)

3. Storage method to magazine

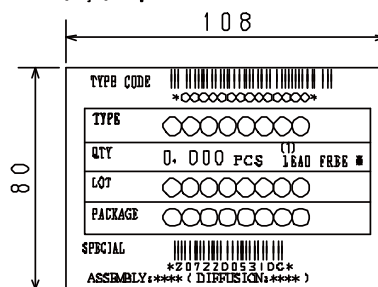


4. Inner box label (unit:mm)



5. Outer box label (unit:mm)

It is a label at the time of factory shipments.  
 The form of a label may change in physical  
 distribution process.



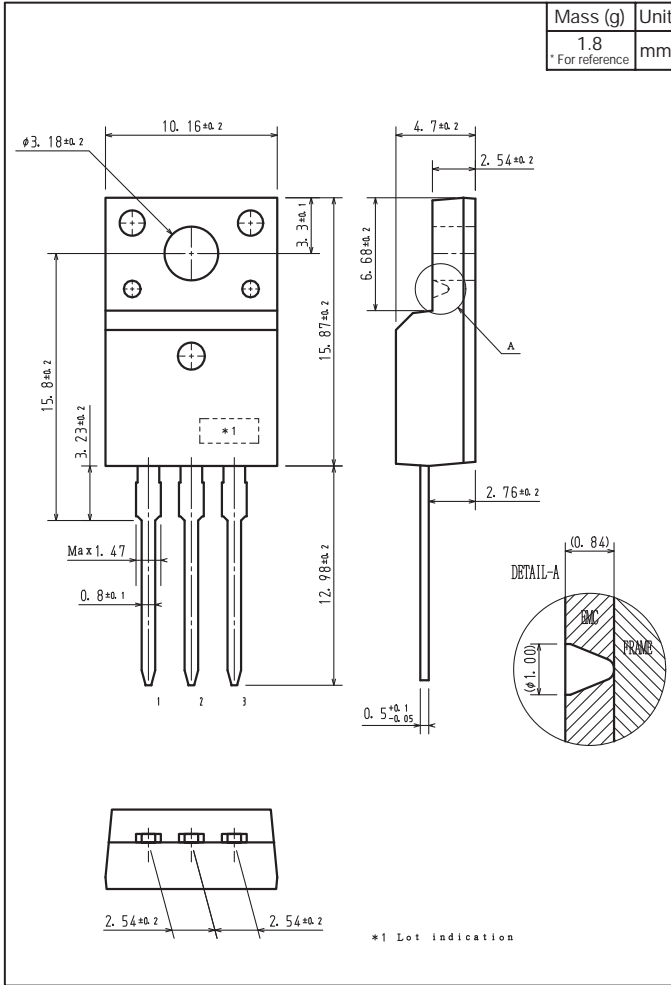
NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

Outline Drawing

2SC6082-1E



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